AMENDMENTS TO THE CLAIMS

This Listing of Claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-25 (canceled).

Claim 26 (original) A method for removing polymer residues on sidewalls of metal lines, comprising:

providing a wafer with at least a metal line layer formed thereon, the sidewalls of the metal lines of the metal line layer having polymer residues formed thereon;

immersing said wafer in a stripping solution for removing the polymer residues in accordance with a first immersion time;

removing said wafer from said stripping solution and maintaining for a first time so that said stripping solution left on said wafer drips down;

immersing said wafer in a first organic solvent for removing said stripping solution left on said wafer in accordance with a second immersion time;

removing said wafer from said first organic solvent and maintaining for a second time so that said striping solution and said first organic solvent left on said wafer drip down;

immersing said wafer in a water flow for removing the stripping solution and said first organic solvent left on said wafer in accordance with a third immersion time; and

removing water left on said wafer in accordance with a predetermined time.

Claim 27 (original) The method of claim 26, wherein said first immersion time is about 10 minutes.

Claim 28 (original) The method of claim 26, wherein said first time is about 100 seconds.

Claim 29 (original) The method of claim 26, wherein said second immersion time is about 5 minutes.

Claim 30 (original) The method of claim 26, wherein said second time is about 50 seconds.

Claim 31 (original) The method of claim 26, wherein said third immersion time is about 10 minutes.

Claim 32 (original) The method of claim 26, wherein said predetermined time is about 10 minutes.

Claim 33 (original) The method of claim 26, wherein said stripping solution comprises alcohol amine, water, dihydoxylbenzene, hydroxyl amine and anticorrosion agent.

Claim 34 (original) The method of claim 26, wherein said first organic solvent comprises alcohol (ROH).

Claim 35 (original) The method of claim 34, wherein said first solvent comprises methanol.

Claim 36 (original) The method of claim 34, wherein said first solvent comprises isopropyl alcohol.

Claim 37 (original) The method of claim 26, wherein prior to immersing said wafer in said water flow, further comprising immersing said wafer in a second organic solvent for further removing said stripping solution left on said wafer in accordance with a fourth immersion time, and removing said wafer from said

second organic solvent and maintaining for a third time so that said stripping solution, said first organic solvent and said second organic solvent drip down.

Claim 38 (original) The method of claim 37, wherein said fourth immersion time is about 5 minutes.

Claim 39 (original) The method of claim 37, wherein said third time is about 50 seconds.

Claim 40 (original) The method of claim 37, wherein said second organic solvent comprises alcohol (ROH).

Claim 41 (original) The method of claim 40, wherein said second organic solvent comprises methanol.

Claim 42 (original) The method of claim 40, wherein said second organic solvent comprises isopropyl alcohol.

Claim 43 (original) The method of claim 26, wherein further comprising providing an inert gas flow in said first organic solvent.

Claim 44 (original) The method of claim 43, wherein said inert gas flow comprises nitrogen gas flow.

Claim 45 (original) The method of claim 43, wherein the flow rate of said inert gas flow is about 15 liters/per minute.

Claim 46 (original) The method of claim 44, wherein the flow rate of said nitrogen gas flow comprises 15 liters/per minute.

Claim 47 (original) The method of claim 37, wherein further comprising providing an insert gas flow in said second organic solvent.

Claim 48 (original) The method of claim 47, wherein said inert gas flow comprises nitrogen gas flow.

Claim 49 (original) The method of claim 47, wherein the flow rate of said inert gas flow is about 15 liters/per minute.

Claim 50 (original) The method of claim 48, wherein the flow rate of said nitrogen gas flow is about 15 liters/per minute.